



ZXMS6005SGQ

60V N-CHANNEL SELF PROTECTED ENHANCEMENT MODE IntelliFET MOSFET

Product Summary

- Continuous Drain Source Voltage V_{DS} = 60V
- On-State Resistance 200mΩ
- Nominal Load Current (V_{IN} = 5V) 2A
- Clamping Energy 480mJ

Description

The ZXMS6005SGQ is a self protected low side IntelliFETTM MOSFET with logic level input. It integrates over-temperature; overcurrent, over-voltage (active clamp) and ESD protected logic level functionality. The ZXMS6005SGQ is ideal as a general purpose switch driven from 3.3V or 5V microcontrollers in harsh environments where standard MOSFETs are not rugged enough.

Applications

- Especially Suited for Loads with a High In-rush Current such as Lamps and Motors
- All Types of Resistive, Inductive and Capacitive Loads in Switching Applications
- µC Compatible Power Switch for 12V DC Applications
- Automotive Rated
- Replaces Electromechanical Relays and Discrete Circuits
- Linear Mode capability the current-limiting protection circuitry is designed to de-activate at low V_{DS} to minimize on state power dissipation. The maximum DC operating current is therefore determined by the thermal capability of the package/board combination, rather than by the protection circuitry. This does not compromise the product's ability to self- protect at low V_{DS}.

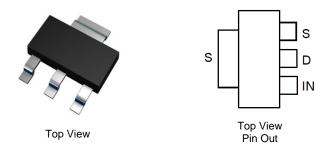
Features and Benefits

- Compact High Power Dissipation Package
- Low Input Current
- Logic Level Input (3.3V and 5V)
- Short Circuit Protection with Auto Restart
- Over Voltage Protection (Active Clamp)
- Thermal Shutdown with Auto Restart
- Over-Current Protection
- Input Protection (ESD)
- High Continuous Current Rating
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT223 (Type DN)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish ³
- Weight: 0.112 grams (Approximate)

SOT223 (Type DN)



Ordering Information (Note 5)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
ZXMS6005SGQTA	ZXMS6005S	7	12	1,000 Units

EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Please refer to https://www.diodes.com/quality/.

5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

Notes:

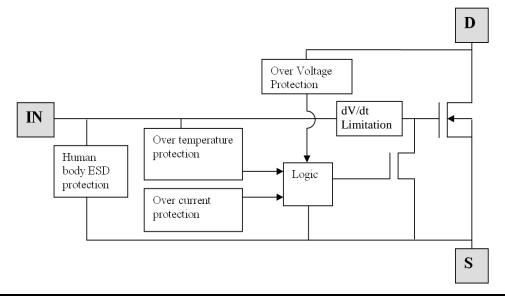


 $\begin{array}{l} {\sf ZXMS6005S} = {\sf Product Type Marking Code} \\ {\sf YWW} = {\sf Date Code Marking} \\ {\sf Y \ or \ } \overline{{\sf Y}} = {\sf Last Digit \ of \ Year \ (ex: 8 = 2018)} \\ {\sf WW \ or \ } \overline{{\sf WW}} = {\sf Week \ Code \ (01 \ to \ 53)} \end{array}$

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Functional Block Diagram



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise stated.)

Characteristic	Symbol	Value	Unit	
Continuous Drain-Source Voltage	V _{DS}	60	V	
Drain-Source Voltage for Short Circuit Protection	V _{DS(SC)}	24	V	
Continuous Input Voltage	V _{IN}	-0.5 to +6	V	
Continuous Input Current @-0.2V \leq V _{IN} \leq 6V Continuous Input Current @V _{IN} $<$ -0.2V or V _{IN} $>$ 6V	lın	No limit I _{IN} ≤2	mA	
Pulsed Drain Current @VIN = 3.3V	I _{DM}	5	А	
Pulsed Drain Current @V _{IN} = 5V	I _{DM}	6	А	
Continuous Source Current (Body Diode) (Note 6)	Is	2.5	А	
Pulsed Source Current (Body Diode)	I _{SM} 10		А	
Unclamped Single Pulse Inductive Energy, T _J = +25°C, I _D = 0.5A, V _{DD} = 24V	E _{AS}	480	mJ	
Electrostatic Discharge (Human Body Model)	V _{ESD}	4000	V	
Charged Device Model	V _{CDM}	1000	V	

Thermal Characteristics (@T_A = +25°C, unless otherwise stated.)

Characteristic	Symbol	Value	Unit
Power Dissipation at $T_A = +25^{\circ}C$ (Note 6) Linear Derating Factor	P _D	1.0 8.0	W mW/°C
Power Dissipation at $T_A = +25^{\circ}C$ (Note 7) Linear Derating Factor	P _D	1.6 12.8	W mW/°C
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	125	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	R _{0JA}	83	°C/W
Thermal Resistance, Junction to Case (Note 8)	R _{eJC}	39	°C/W
Operating Temperature Range	TJ	-40 to +150	°C
Storage Temperature Range	T _{STG}	-55 to +150	°C

Notes: 6. For a device surface mounted on 15mm x 15mm single sided 1oz weight copper on 1.6mm FR-4 board, in still air conditions. Sink split drain 80% and source 20% to isolate connections.

7. For a device surface mounted on 50mm x 50mm single sided 2oz weight copper on 1.6mm FR-4 board, in still air conditions. Sink split drain 80% and source 20% to isolate connections.

8. Thermal resistance between junction and the mounting surfaces of drain and source pins.

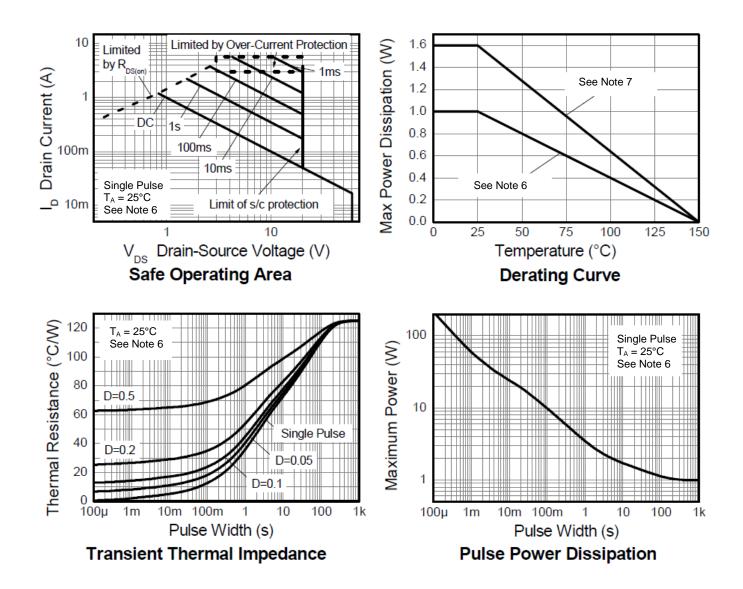


Recommended Operating Conditions

The ZXMS6005SGQ is optimized for use with μ C operating from 3.3V and 5V supplies.

Characteristic	Symbol	Min	Max	Unit
Input Voltage Range	V _{IN}	0	5.5	V
Ambient Temperature Range	T _A	-40	+125	°C
High Level Input Voltage for MOSFET to be on	VIH	3	5.5	V
Low Level Input Voltage for MOSFET to be off	VIL	0	0.7	V
Peripheral Supply Voltage (voltage to which load is referred)	VP	0	24	V

Thermal Characteristics





Electrical Characteristics (@T_A = +25°C, unless otherwise stated.)

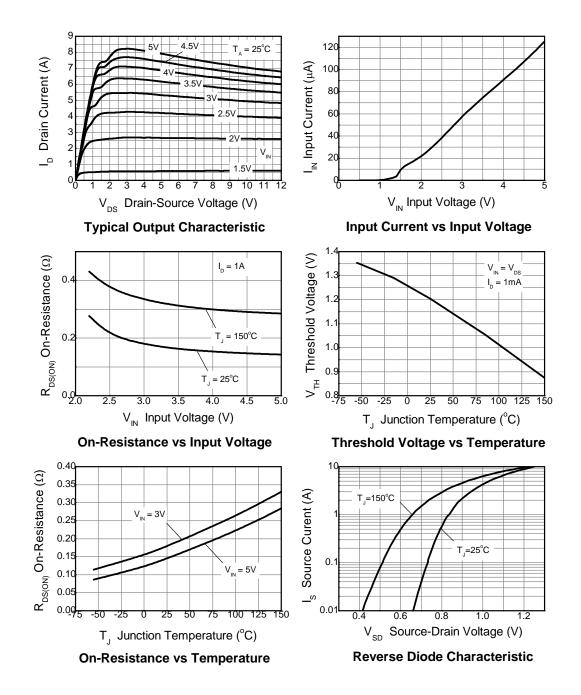
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Static Characteristics				•		
Drain-Source Clamp Voltage	V _{DS(AZ)}	60	65	70	V	$I_D = 10 \text{mA}$
Off State Drain Correct	I _{DSS}	_	—	1	μA	$V_{DS} = 12V, V_{IN} = 0V$
Off State Drain Current		_	—	2		$V_{DS} = 36V, V_{IN} = 0V$
Input Threshold Voltage	V _{IN(TH)}	0.7	1.2	1.5	V	$V_{DS} = V_{GS}, I_D = 1mA$
least Querent		_	60	100	μA	$V_{IN} = 3V$
Input Current	lin	_	120	200		$V_{IN} = 5V$
Input Current While Over Temperature Active	—	_	—	300	μA	$V_{IN} = 5V$
	_	_	170	250	mΩ	$V_{IN} = 3V, I_D = 1A$
Static Drain-Source On-State Resistance	R _{DS(ON)}	_	150	200		$V_{IN} = 5V, I_D = 1A$
Continuous Durin Coursent (Nata C)		1.4	_	—	A	$V_{IN} = 3V, T_A = +25^{\circ}C$
Continuous Drain Current (Note 6)		1.6	—	—		$V_{IN} = 5V, T_A = +25^{\circ}C$
Continuous Drain Current (Note 7)	ID	1.9	—	—		$V_{IN} = 3V, T_A = +25^{\circ}C$
Continuous Drain Current (Note 7)		2.0	—	—		$V_{IN} = 5V, T_A = +25^{\circ}C$
Current Limit (Note 9)	I _{D(LIM)}	2.2	5	—	A	$V_{IN} = 3V$
		3.3	7	_		$V_{IN} = 5V$
Dynamic Characteristics						
Turn On Delay Time	t _{D(ON)}		6	—		
Rise Time	t _R	-	14	_	μs	$V_{DD} = 12V, I_D = 1A, V_{GS} = 5V$
Turn Off Delay Time	t _{D(OFF)}	_	34			
Fall Time	t _F	_	19	—		
Over-Temperature Protection	•		•	•	•	
Thermal Overload Trip Temperature (Note 10)	T _{JT}	+150	+175	_	°C	—
Thermal Hysteresis (Note 10)	—	_	+10		°C	_

Notes: 9. The drain current is restricted only when the device is in saturation (see graph 'Typical Output Characteristic'). This allows the device to be used in the fully on state without interference from the current limit. The device is fully protected at all drain currents, as the low power dissipation generated outside saturation makes current limit unnecessary.

10. Over-temperature protection is designed to prevent device destruction under fault conditions. Fault conditions are considered as "outside" normal operating range, so this part is not designed to withstand over-temperature for extended periods.

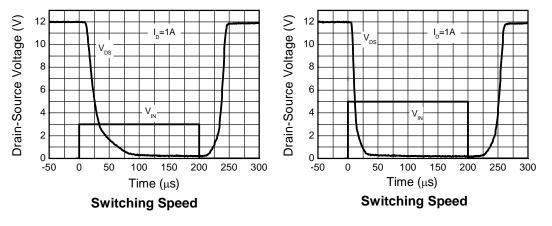


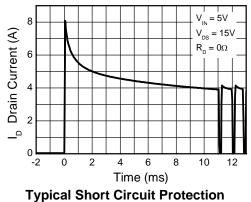
Typical Characteristics





Typical Characteristics (Cont.)



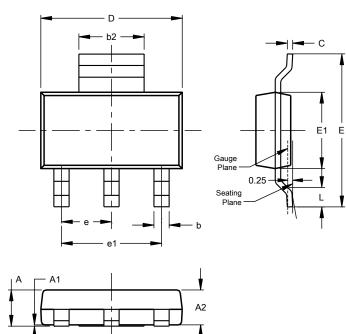




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223 (Type DN)

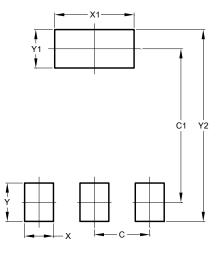


SC	SOT223 (Type DN)					
Dim	Min	Max	Тур			
Α		1.70				
A1	0.01	0.15				
A2	1.50	1.68	1.60			
b	0.60	0.80	0.70			
b2	2.90	3.10				
С	0.20	0.32				
D	6.30	6.70				
E	6.70	7.30				
E1	3.30	3.70				
е			2.30			
e1			4.60			
L	0.85					
All	All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223 (Type DN)



Dimensions	Value (in mm)		
С	2.30		
C1	6.40		
Х	1.20		
X1	3.30		
Y	1.60		
Y1	1.60		
Y2	8.00		



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